

## OptiMOS™3 Power-Transistor

### Features

- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21

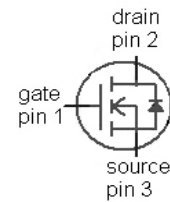


Halogen-Free

### Product Summary

|                         |     |    |
|-------------------------|-----|----|
| $V_{DS}$                | 100 | V  |
| $R_{DS(on),max}$ TO-263 | 18  | mΩ |
| $I_D$                   | 43  | A  |

| Type    | IPP180N10N3 G                                                                       | IPI180N10N3 G                                                                       |
|---------|-------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|         |  |  |
| Package | PG-TO220-3                                                                          | PG-TO262-3                                                                          |
| Marking | 180N10N                                                                             | 180N10N                                                                             |



**Maximum ratings**, at  $T_J=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol            | Conditions                               | Value       | Unit |
|-------------------------------------|-------------------|------------------------------------------|-------------|------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}^{2)}$                  | 43          | A    |
|                                     |                   | $T_C=100\text{ °C}$                      | 30          |      |
| Pulsed drain current <sup>2)</sup>  | $I_{D,pulse}$     | $T_C=25\text{ °C}$                       | 172         |      |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=33\text{ A}$ , $R_{GS}=25\text{ Ω}$ | 50          | mJ   |
| Gate source voltage                 | $V_{GS}$          |                                          | ±20         | V    |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$                       | 71          | W    |
| Operating and storage temperature   | $T_J$ , $T_{stg}$ |                                          | -55 ... 175 | °C   |
| IEC climatic category; DIN IEC 68-1 |                   |                                          | 55/175/56   |      |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> See figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                           |            |                                              |   |   |     |     |
|-------------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case       | $R_{thJC}$ |                                              | - | - | 2.1 | K/W |
| Thermal resistance,<br>junction - ambient | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                           |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 40  |     |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |                                                             |     |      |     |               |
|----------------------------------|---------------|-------------------------------------------------------------|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                        | 100 | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=33\text{ }\mu\text{A}$                  | 2   | 2.7  | 3.5 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.1  | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 10   | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                     | -   | 1    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=33\text{ A}$                       | -   | 15.5 | 18  | m $\Omega$    |
|                                  |               | $V_{GS}=6\text{ V}, I_D=16\text{ A}$                        | -   | 19.3 | 33  |               |
| Gate resistance                  | $R_G$         |                                                             | -   | 1.4  | -   | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=33\text{ A}$             | 20  | 40   | -   | S             |

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |                                                                                 |   |      |      |    |
|------------------------------|--------------|---------------------------------------------------------------------------------|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$<br>$f=1\text{ MHz}$                    | - | 1350 | 1800 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                 | - | 237  | 315  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                 | - | 11   | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=33\text{ A}, R_G=1.6\ \Omega$ | - | 12   | -    | ns |
| Rise time                    | $t_r$        |                                                                                 | - | 12   | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                 | - | 19   | -    |    |
| Fall time                    | $t_f$        |                                                                                 | - | 5    | -    |    |

**Gate Charge Characteristics<sup>6)</sup>**

|                       |               |                                                                            |   |     |    |    |
|-----------------------|---------------|----------------------------------------------------------------------------|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=50\text{ V}, I_D=33\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 7   | -  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                            | - | 4   | -  |    |
| Switching charge      | $Q_{sw}$      |                                                                            | - | 6   | -  |    |
| Gate charge total     | $Q_g$         |                                                                            | - | 19  | 25 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                            | - | 4.9 | -  | V  |
| Output charge         | $Q_{oss}$     | $V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$                                    | - | 25  | 33 | nC |

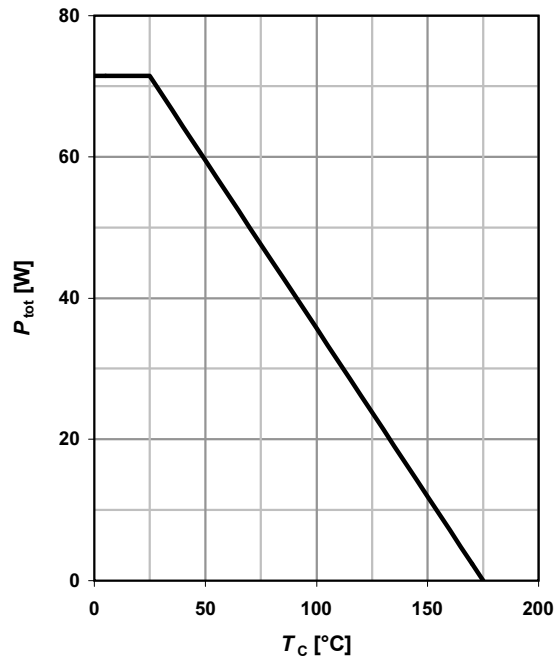
**Reverse Diode**

|                                  |               |                                                                           |   |    |     |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ °C}$                                                        | - | -  | 43  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -  | 172 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=33\text{ A},$<br>$T_j=25\text{ °C}$               | - | 1  | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=15\text{ V}, I_F=33\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 55 | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | 92 | -   | nC |

<sup>6)</sup> See figure 16 for gate charge parameter definition

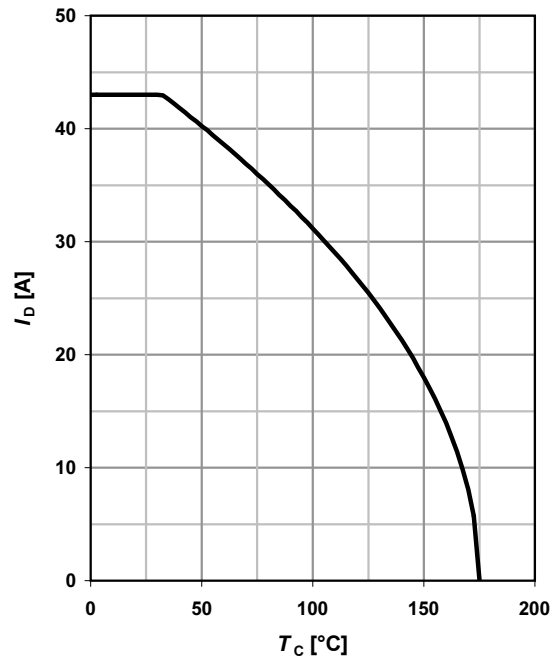
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

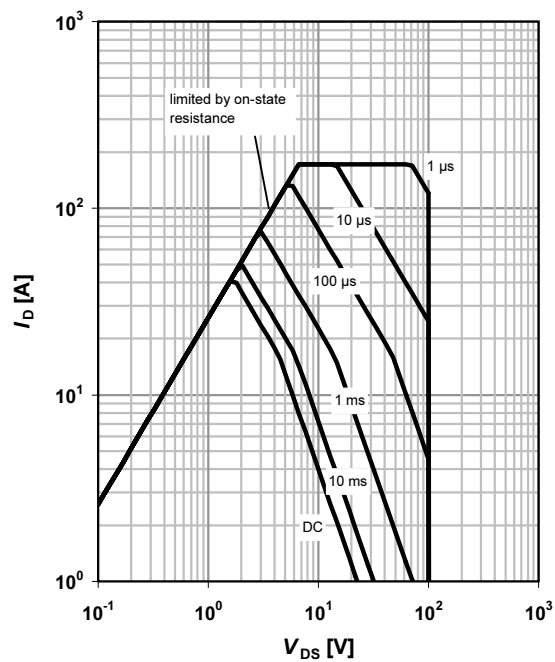
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

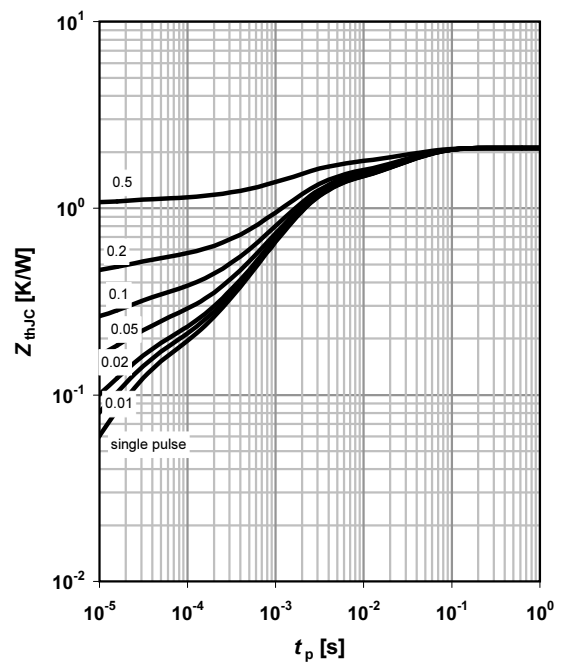
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

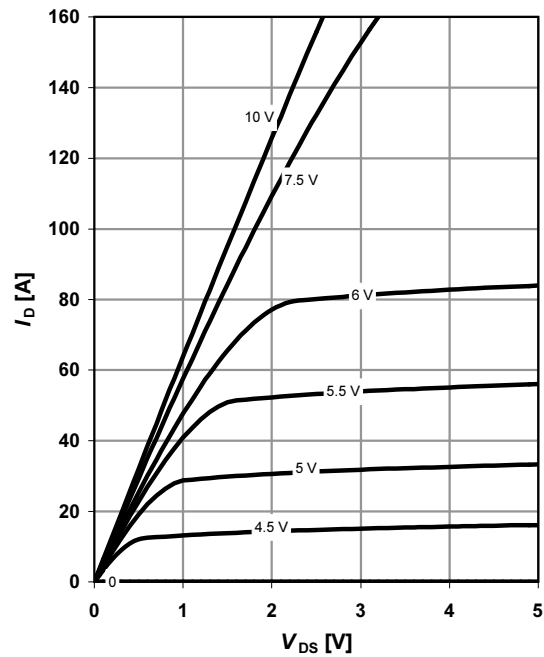
parameter:  $D = t_p / T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

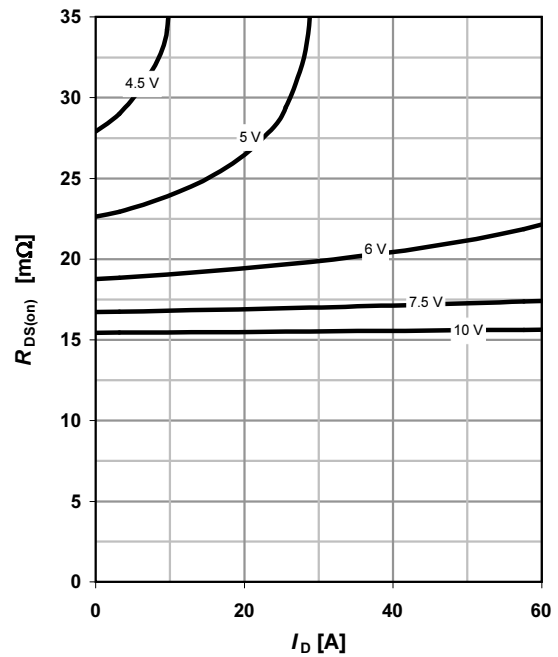
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_J = 25^\circ\text{C}$$

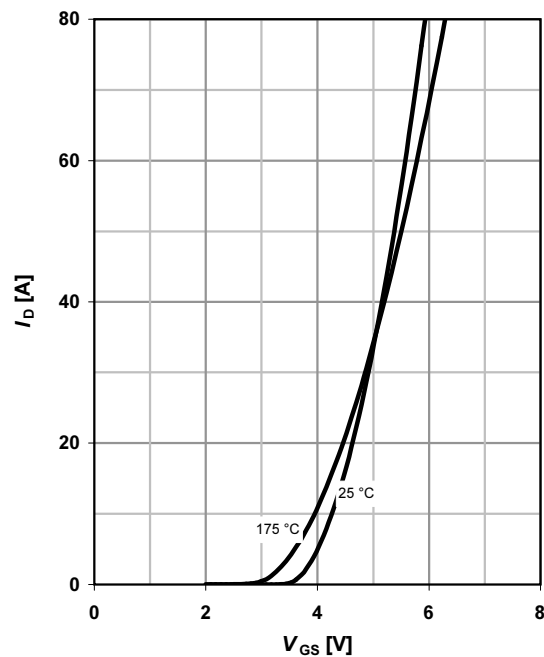
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

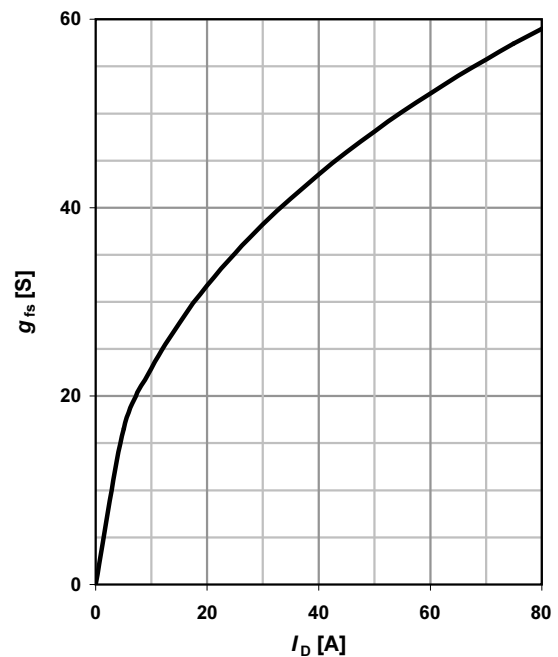
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_J$



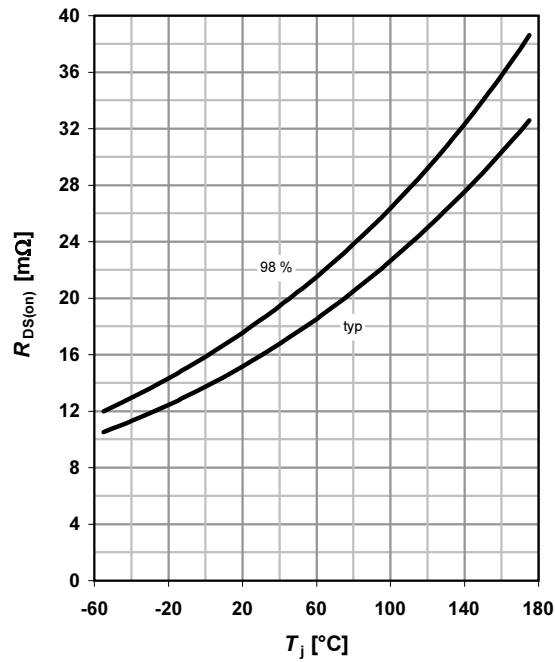
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$



### 9 Drain-source on-state resistance

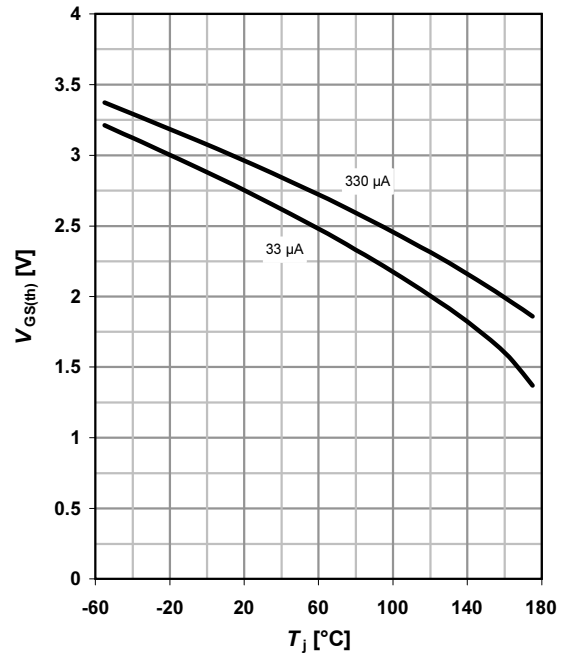
$$R_{DS(on)} = f(T_j); I_D = 33 \text{ A}; V_{GS} = 10 \text{ V}$$



### 10 Typ. gate threshold voltage

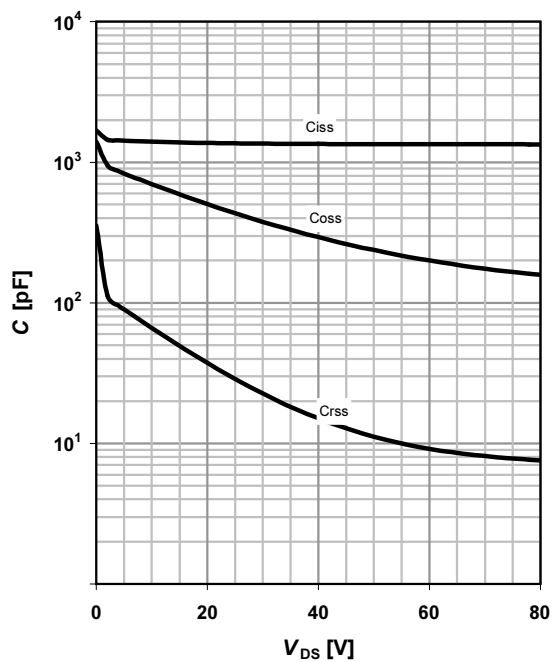
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



### 11 Typ. capacitances

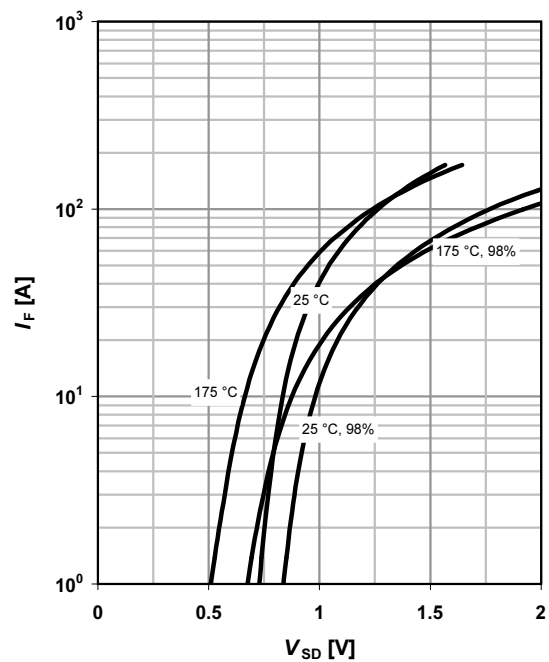
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



### 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

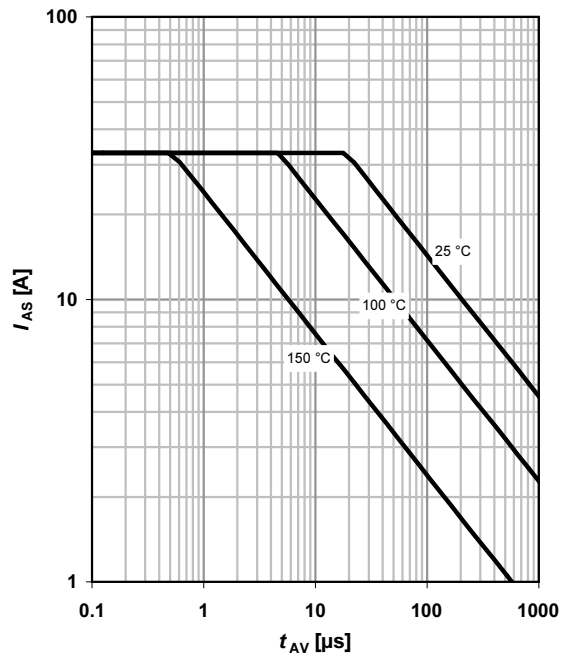
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

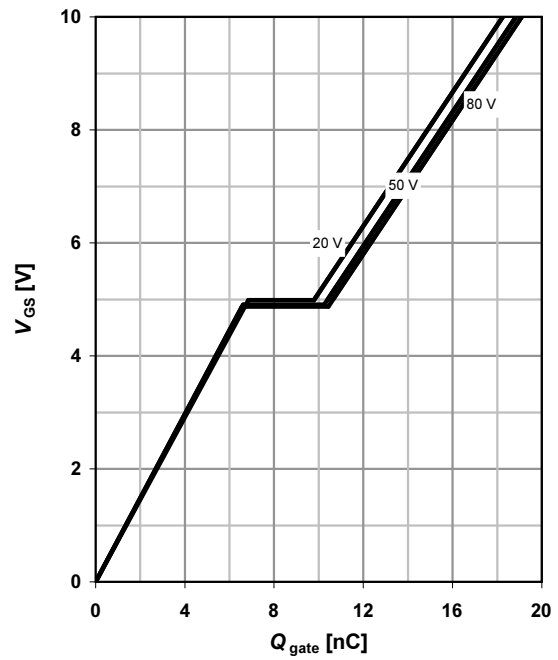
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

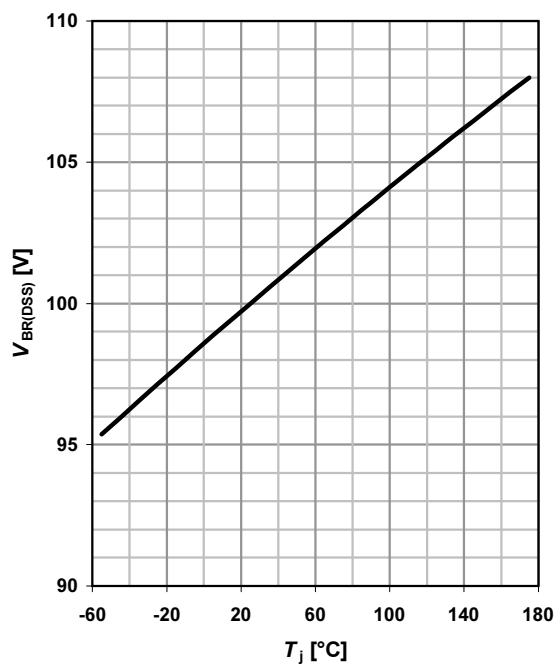
$$V_{GS}=f(Q_{\text{gate}}); I_D=33\ \text{A pulsed}$$

parameter:  $V_{DD}$

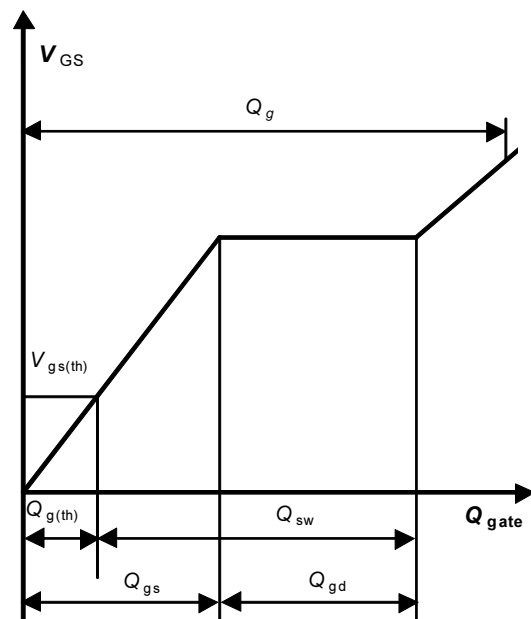


### 15 Drain-source breakdown voltage

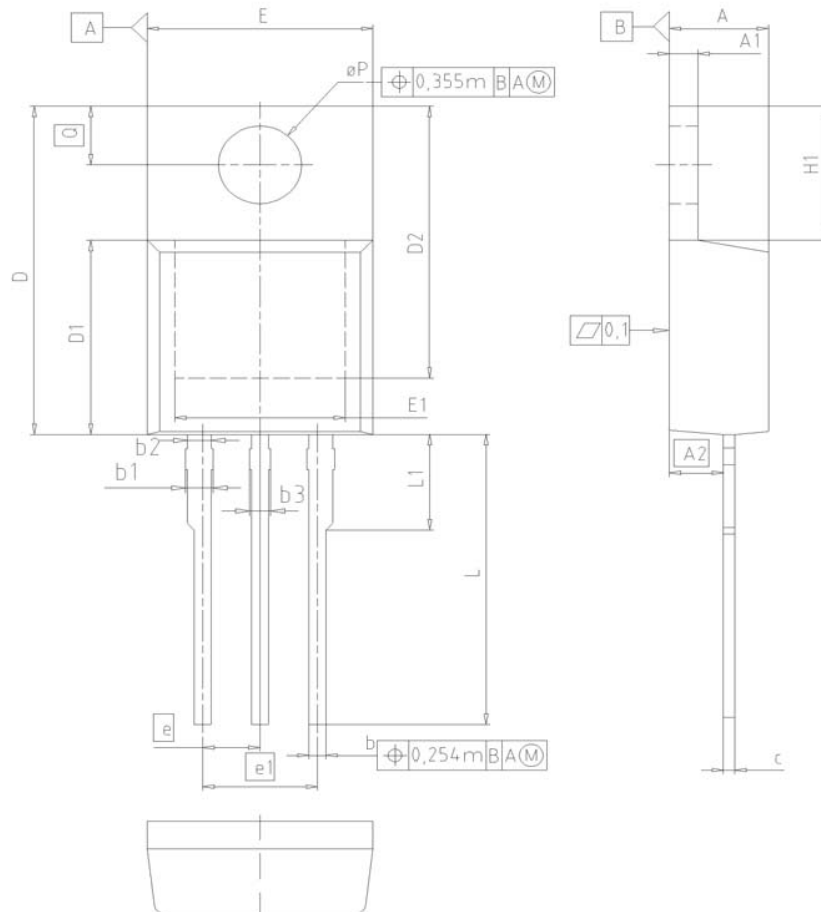
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



### 16 Gate charge waveforms

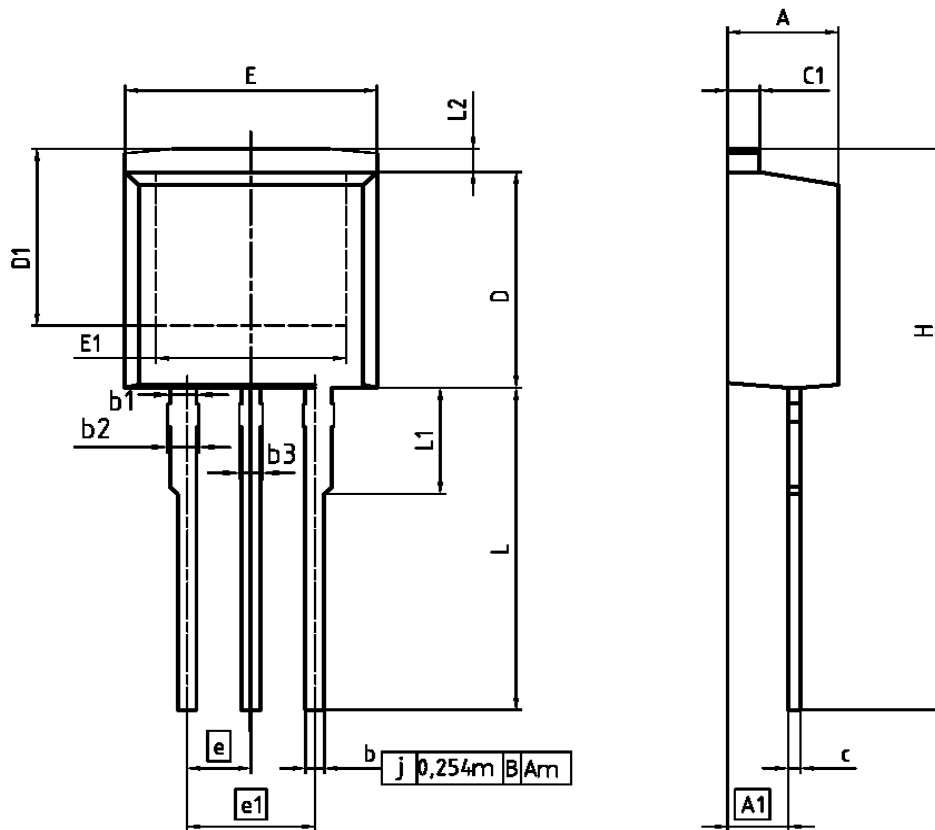


## PG-TO-220



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 1.17        | 1.40  | 0.046  | 0.055 |
| A2  | 2.15        | 2.72  | 0.085  | 0.107 |
| b   | 0.65        | 0.86  | 0.026  | 0.034 |
| b1  | 0.95        | 1.40  | 0.037  | 0.055 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| b3  | 0.65        | 1.15  | 0.026  | 0.045 |
| c   | 0.33        | 0.60  | 0.013  | 0.024 |
| D   | 14.81       | 15.95 | 0.583  | 0.628 |
| D1  | 8.51        | 9.45  | 0.335  | 0.372 |
| D2  | 12.19       | 13.10 | 0.480  | 0.516 |
| E   | 9.70        | 10.36 | 0.382  | 0.408 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H1  | 5.90        | 6.90  | 0.232  | 0.272 |
| L   | 13.00       | 14.00 | 0.512  | 0.551 |
| L1  | -           | 4.80  | -      | 0.189 |
| øP  | 3.60        | 3.89  | 0.142  | 0.153 |
| Q   | 2.60        | 3.00  | 0.102  | 0.118 |

|                                    |
|------------------------------------|
| <b>DOCUMENT NO.</b><br>Z8B00003318 |
| <b>SCALE</b><br>0 2.5 5mm          |
| <b>EUROPEAN PROJECTION</b>         |
| <b>ISSUE DATE</b><br>23-08-2007    |
| <b>REVISION</b><br>05              |



| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 4.300       | 4.572  | 0.169  | 0.180 |
| A1  | 2.150       | 2.718  | 0.085  | 0.107 |
| b   | 0.650       | 0.864  | 0.026  | 0.034 |
| b1  | 0.950       | 1.093  | 0.037  | 0.043 |
| b2  | 0.950       | 1.400  | 0.037  | 0.055 |
| b3  | 0.650       | 1.118  | 0.026  | 0.044 |
| c   | 0.330       | 0.600  | 0.013  | 0.024 |
| c1  | 1.170       | 1.400  | 0.046  | 0.055 |
| D   | 8.509       | 8.450  | 0.335  | 0.372 |
| D1  | 6.900       | -      | 0.272  | -     |
| E   | 9.700       | 10.363 | 0.382  | 0.408 |
| E1  | 6.500       | 8.600  | 0.256  | 0.339 |
| e   | 2.540       |        | 0.100  |       |
| e1  | 5.080       |        | 0.200  |       |
| N   | 3           |        | 3      |       |
| L   | 13.000      | 14.000 | 0.512  | 0.551 |
| L1  | -           | 4.800  | -      | 0.189 |
| L2  | -           | 1.727  | -      | 0.068 |

|                          |
|--------------------------|
| REFERENCE<br>JEDEC TO262 |
| SCALE 0 2.5 5mm          |
| EUROPEAN PROJECTION      |
| ISSUE DATE<br>05-05-2006 |
| FILE<br>TO262_1          |

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